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Strain-induced magnetization control in an oxide multiferroic heterostructure

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Controlling magnetism by using electric fields is a goal of research towards novel spintronic devices and future nanoelectronics. For this reason, multiferroic heterostructures attract much interest. Here we provide experimental evidence, and supporting density functional theory analysis, of a transition in $\text{La}_{0.65}\text{Sr}_{0.35}\text{MnO}_3$ thin film to a stable ferromagnetic phase, that is induced by the structural and strain properties of the ferroelectric BaTiO_3 (BTO) substrate, which can be modified by applying external electric fields. X-ray magnetic circular dichroism measurements on Mn L edges with a synchrotron radiation show, in fact, two magnetic transitions as a function of temperature that correspond to structural changes of the BTO substrate. We also show that ferromagnetism, absent in the pristine condition at room temperature, can be established by electrically switching the BTO ferroelectric domains in the out-of-plane direction. The present results confirm that electrically induced strain can be exploited to control magnetism in multiferroic oxide heterostructures.

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I. INTRODUCTION

After revolutionizing data storage technology, control of electron spin is now close to being implemented in nanotechnology for applications in computation, communication, and energy harvesting [1,2]. To realize such innovative spintronic devices, one of the key challenges is to find reliable, fast, and energy efficient ways to manipulate the magnetic state in a material or heterostructure. Controlling (ferro)magnetism via application of an electric field appears very attractive as no large power-dissipating currents [3,4] are needed in principle. Electric field control of magnetism has been obtained in multiferroics [5] but they usually display a weak ferromagnetic response [6,7]. To overcome this limitation, the use of artificial heterostructures combining ferromagnetic films with ferro- or piezo-electric substrates has been explored [8–12].

Transition-metal oxides with perovskite structure are promising in this context, as they display strong correlation between spin, charge, orbital, and lattice degrees of freedom, thus potentially providing multiple ways to influence magnetism [13–15]. It has been previously shown that the total magnetic moment [16,17], the coercive field [18], the magnetic anisotropy [19,20], and the Curie temperature [17,21] can be modified by applying electric fields to oxide heterostructures. A magnetic transition within the thickness of a few unit cells driven by charge accumulation at the manganite/ferroelectric interface was also demonstrated [22]. However, the possibility to use strain to reversibly drive a magnetic transition on a longer scale is still worth exploring, both for fundamental scientific interest and potential practical applications.

We show here the results of element-specific magnetometry on $\text{BaTiO}_3/\text{La}_{1-x}\text{Sr}_x\text{MnO}_3$ (BTO/LSMO) epitaxial heterostructure grown by molecular beam epitaxy, as a function of the modified strain of the substrate, which reversibly triggers phase transitions in the LSMO overlayer. The applied strain is tuned employing the intrinsic structural transition of the substrate for changing temperature, as well as switching its ferroelectric domains with an electric bias. The main result is the development of ferromagnetism at 300 K in LSMO driven by BTO poling.

The phase diagram of ferroelectric BTO displays four crystal structures, that are stable at different temperatures [23,24]. The rhombohedral (R, below 180 K), orthorhombic (O, between 180 and 280 K), and tetragonal (T, up to 410 K) phases are all ferroelectric, with the polarization vector pointing along [111], [011], and [001] pseudocubic directions, respectively. A structural phase transition into a cubic, nonferroelectric lattice, takes place at 410 K. LSMO presents a complex phase diagram, displaying ferromagnetic as well as various kinds of antiferromagnetic order depending on temperature and La/Sr ratio [25]. The magnetic state of LSMO is reflected in its transport properties. [26] For the Sr-doping concentration $x = 1/3$, bulk LSMO is ferromagnetic and metallic with Curie temperature above room temperature (around 370 K). However, the physical properties of LSMO can be tuned also by means of epitaxial strain [27,28], and are therefore affected by the BTO structural phase and polarization orientation [19].

We have grown ultrathin (30 u.c. \approx 12 nm) films of LSMO by UHV molecular beam epitaxy on top of a BTO substrate obtaining fully epitaxial heterostructure, as demonstrated by reflection high-energy electron-diffraction (RHEED) images acquired during the deposition. We have probed the magnetic

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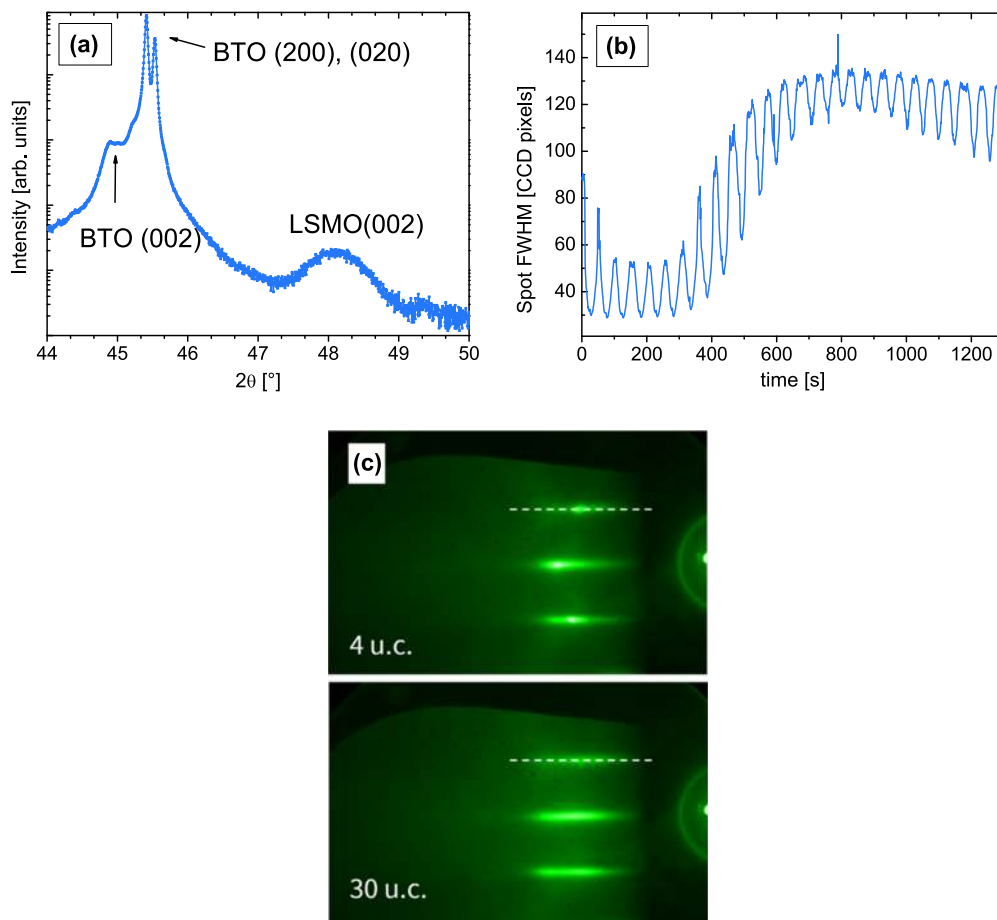


FIG. 1. (a) $\theta - 2\theta$ scan of the LSMO/BTO sample, acquired at room temperature in a high-intensity configuration. It is possible to distinguish the different domains of BTO crystal in the tetragonal phase, both out of plane and in plane. Note that BTO peaks are split into two components because of the presence of both $K_{\alpha 1}$ and $K_{\alpha 2}$ lines in the Cu x-ray source. (b) Evolution of the full width at half maximum of RHEED diffraction spots during the growth of LSMO, starting from the fifth unit cell. (c) RHEED images acquired *in situ* during LSMO growth, after completing the 4th and 30th unit cell. The plot in Fig. 1(b) was obtained from the profile along the dashed lines.

85 properties of the LSMO by measuring x-ray magnetic circular
 86 dichroism (XMCD) on the Mn $L_{2,3}$ edge at the Advanced
 87 Photoelectric Effect beamline high-energy branch (APE-HE)
 88 of the Elettra synchrotron radiation facility in Trieste, Italy
 89 [29,30]. LSMO is observed to undergo magnetic transitions
 90 when changing the temperature and, at 300 K, when applying
 91 electric bias. X-ray-diffraction (XRD) measurements in Bragg-
 92 Brentano geometry show that these effects on the overlayer are
 93 correlated to the structural changes of the BTO substrate, i.e.,
 94 are connected with modifications of the interface constraints.
 95 *Ab initio* density functional theory (DFT) simulations, as
 96 implemented with the QUANTUM ESPRESSO code, have been
 97 performed, giving independent support of the reproducible
 98 observation of strain-mediated magnetic transitions in the
 99 LSMO layer.

100 II. EXPERIMENTAL RESULTS

101 We concentrate the analysis on LSMO thin films (doping
 102 level $x = 0.35$, thickness 30 u.c.) grown epitaxially on a BTO
 103 crystalline substrate (thickness 1 mm).

104 Figure 1(a) shows the XRD $\theta - 2\theta$ diffraction scan in
 105 high-intensity mode at room temperature for as-deposited

106 LSMO/BTO. Nonpolarized BTO shows the expected presence
 107 of domains elongated both in plane, i.e., (100) and/or (010), and
 108 out of plane, (001), in T phase. The corresponding calculated
 109 lattice parameters of BTO are 3.991 and 4.035 Å respectively,
 110 in perfect agreement with the data reported in literature [23,24].
 111 By comparing the relative intensities of the in-plane and
 112 out-of-plane peaks, we infer that the majority of domains are
 113 oriented in plane.

114 Regarding the LSMO thin layer, its (002) peak indicates a
 115 pseudocubic out-of-plane lattice parameter of 3.78 Å, much
 116 smaller compared to the bulk value of 3.87 Å. [31] This is due
 117 to the substrate-induced in-plane tensile strain, which causes a
 118 decrease of the out-of-plane lattice parameter. The full width at
 119 half maximum (FWHM) of the RHEED (01) diffraction spot,
 120 shown in Fig. 1(b), was recorded to monitor the dynamics of the
 121 crystalline structure of the film. A broadening of the diffraction
 122 spots is observed after 10 u.c., a symptom of the increasing
 123 disorder originating from the formation of defects and/or
 124 surface roughening. A further effect to be considered is the
 125 domain structure and mosaicity of the substrate. The formation
 126 of defects for increasing thickness can be expected given the
 127 large mismatch (2.6–3.3%, depending on the structural phase)
 128 between BTO and LSMO, and may accompany the tendency to

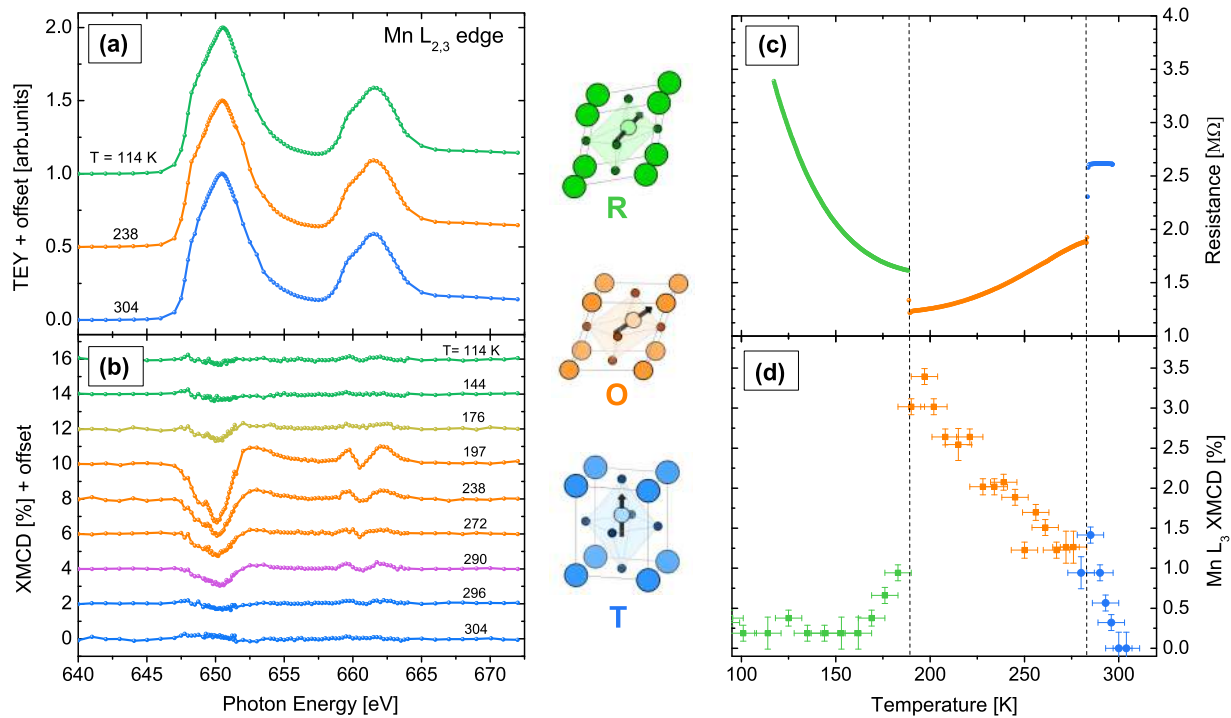


FIG. 2. Mn $L_{2,3}$ XAS (a) and XMCD (b) spectra acquired for various temperatures corresponding to different BTO structural phases, for the pristine case. The XAS curves shown are the sum of the two absorption spectra measured after magnetic field saturation with opposite field directions. Temperature dependence of LSMO/BTO resistance (c) and XMCD signal on the Mn L_3 edge (d) with BTO in the pristine state. Dashed lines correspond to BTO structural transitions.

change the lattice parameters towards bulk values (relaxation). However, given the value of the out-of-plane lattice parameter measured, the film appears to be far from the fully relaxed bulk structure, and still clamped to the substrate. Using the Poisson ratio $\nu = 0.36$ reported in literature [32], an expanded in-plane lattice parameter of 3.90 \AA is calculated. A reciprocal space map around the (103) reflection is presented and discussed in the Supplemental Material [33]. These data testify a partial relaxation of the LSMO film. We notice that the (103) reflection of the film is very low, possibly because of the poor quality of the BTO substrate.

Figures 2(a) and 2(b) show the absorption spectra and corresponding XMCD curves of the unpolarized LSMO/BTO sample. The XMCD values expressed in percent have been corrected taking into account the angle of 45° between the incident beam light and the direction of the in-plane applied magnetic field, as well as the 75% circular polarization degree of our undulator light.

The x-ray-absorption (XAS) spectrum presents two broad multiplets, due to the large Mn $3d$ bandwidth, as expected and previously reported for optimally doped LSMO [34–36]. When passing across the BTO structural transitions, no changes were observed in the Mn $L_{2,3}$ line shape, as shown in Fig. 2(a). However, a clear change was observed in the corresponding dichroism, as shown in Fig. 2(b): for the BTO rhombohedral ($T < 180 \text{ K}$, in green) and tetragonal ($T > 280 \text{ K}$, blue) phases no dichroism was detected in the LSMO overlayer, but in the orthorhombic phase (orange) a XMCD signal of 3% is clearly detected. The measured multiplet structure corresponds to what was reported in literature for optimally doped LSMO thin films [17,37]. These results show that even if the structural

phase of the BTO substrate does not modify the chemical environment of Mn in LSMO it does affect its magnetic ordering.

Figure 2(c) shows the electric transport measurements of LSMO/BTO in the temperature range between 120 and 300 K obtained with the four-probes method in van der Pauw configuration. We observe jumps of resistance values in correspondence of all the BTO structural transitions. Such sharp transitions were also reported for thicker LSMO layers on BTO [19]. The transport properties are well correlated with the magnetic changes observed with XMCD. In the O phase the resistance increases with temperature, which is typical of a metallic behavior, whereas in the R phase it decreases, as expected for a semiconductor/insulator. It is known that in LSMO there is a strong connection between electric transport and magnetic ordering, due to the double-exchange mechanism, so that ferromagnetism is related to a metallic phase whereas the insulator behavior is a sign of lack of ferromagnetic order [38]. This is confirmed also in our case, with a perfect correlation between transport and XMCD measurements [Fig. 2(d)]. The LSMO magnetic transitions measured in correspondence of the structural transitions of BTO proved to be perfectly reproducible and independent of the thermal history of the sample. Consistent data were measured during the cooling of the sample.

Upon out-of-plane polarization of BTO at room temperature, a similar evolution of the XMCD signal with temperature was observed: no dichroism was detected in the lowest temperature range (BTO in the R phase) but a clear signal of magnetic dichroism was detected for BTO in the O phase. This XMCD signal was measured also without external magnetic field by reversing the light circular polarization handedness, as well as

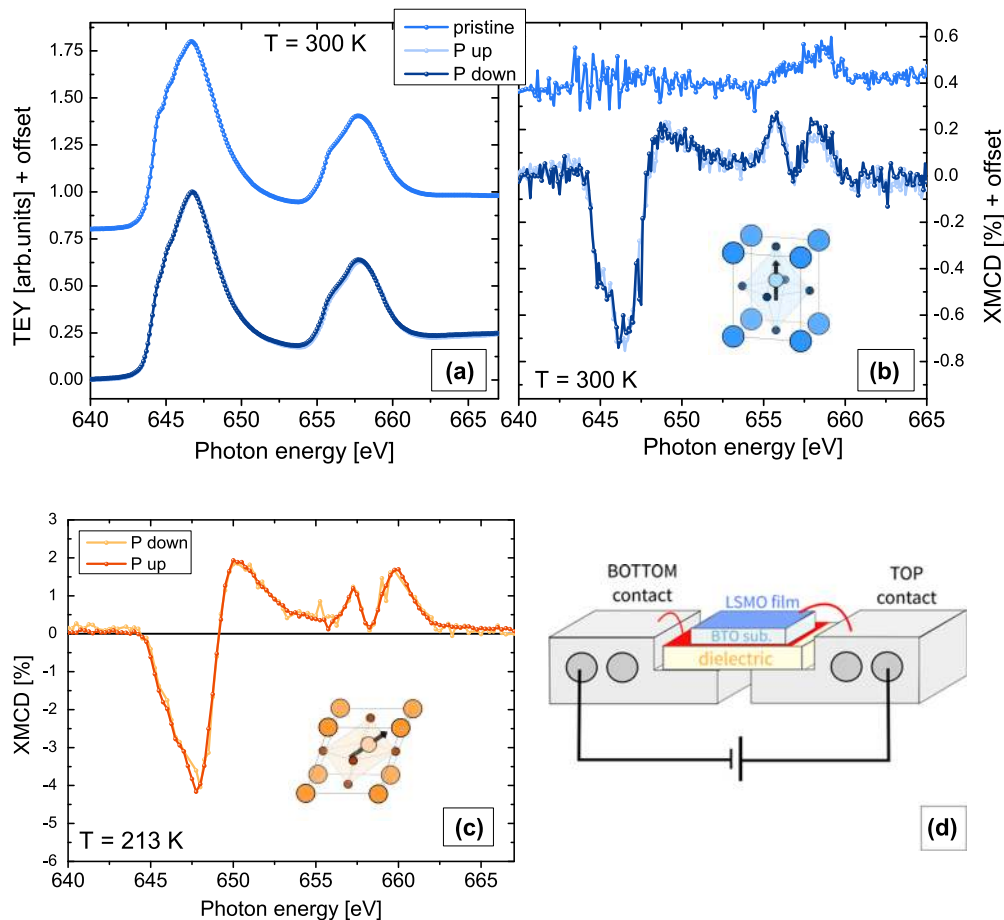


FIG. 3. Comparison of the Mn $L_{2,3}$ XAS (a) and XMCD (b) spectra for BTO in the pristine state and polarized with positive or negative bias in T phase. (c) Comparison of the XMCD spectra for BTO polarized with positive/negative bias, in the O phase. (d) Schematic of the sample holder used for *in situ* polarization of BTO. Contacts with the sample holder (in red) were made with silver paint. The dielectric spacer was inserted to avoid shorts between the two parts of the sample holder.

191 when the sample reached this state being warmed up from the
 192 nonferromagnetic R phase. This shows that the LSMO film
 193 acquires a spontaneous remanent magnetization after the BTO
 194 R-O phase transition.

195 A smaller but clearly detected XMCD signal, in the range
 196 0.5–1%, was also measured at room temperature, which was
 197 absent in the pristine nonpolarized system [Fig. 3(b)]. This
 198 variation in the LSMO magnetization is again not reflected
 199 in changes in the XAS line shape, as shown in Fig. 3(a). No
 200 differences could be detected in the spectra when reversing
 201 the direction of the polarization for all the BTO structural
 202 phases. This was verified both at room temperature [as shown
 203 in Fig. 3(b)] and with BTO in the O phase, for which the
 204 highest dichroic signal is observed [Fig. 3(c)]. The effective
 205 change of the polarization state was monitored acquiring a
 206 current vs voltage curve (see Supplemental Material [33]).
 207 The unchanging XAS/XMCD spectrum is compatible with en-
 208 tirely strain-driven magnetic phenomena, and excludes charge
 209 accumulation/depletion effects at the BTO-LSMO interface as
 210 a possible origin.

211 In order to observe the structural variations of BTO after
 212 setting the out-of-plane electric polarization, HR-XRD $\theta - 2\theta$
 213 scans of LSMO/BTO were performed. First, the sample was
 214 set in the high-temperature cubic phase, then cooled down

to room temperature (tetragonal phase); the measurements
 215 were performed both without applied bias voltage (light curve
 216 in Fig. 4) and with an out-of-plane applied electric field of
 217 400 V (dark curve). Unpolarized BTO presents a combination
 218 of in-plane (100) and (010) and out-of-plane (001) domains,
 219 as sketched in the insets of Fig. 4. When an electric field is
 220 applied along the c axis (perpendicular to the surface), BTO
 221 aligns its dielectric polarization, which implies shrinking the
 222 in-plane lattice parameter and expanding the out-of-plane one.
 223 The ratio between the two domains changes consequently,
 224 and most domains are set in the (001) direction: the $\theta - 2\theta$
 225 scans show a dramatic change in the out-of-plane/in-plane
 226 peak heights, which is compatible with the out-of-plane rotation
 227 of the ferroelectric domains. The same effect is expected to occur
 228 when applying a voltage at a fixed temperature, consistently
 229 with previous observations by Eerenstein *et al.* [16]. This was
 230 done during our XMCD measurements.
 231

III. AB INITIO CALCULATIONS

232 DFT calculations of strained LSMO were performed in
 233 order to gain a better understanding of the complex ob-
 234 served phenomenology. A $\sqrt{2} \times \sqrt{2} \times 2$ cell with tetrago-
 235 nal/orthorhombic $Pnma$ symmetry was assumed, with generic
 236

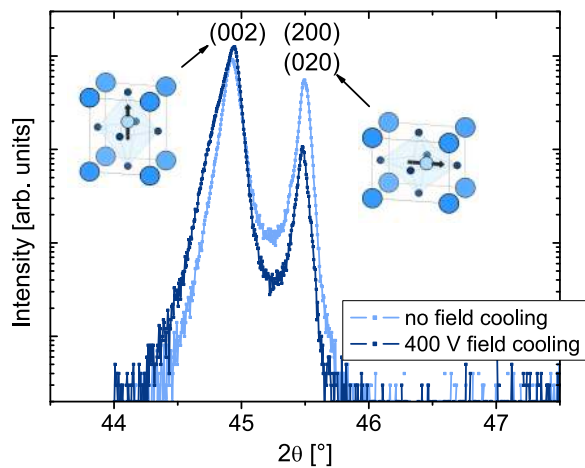


FIG. 4. $\theta - 2\theta$ scans in high-resolution configuration of the LSMO/BTO sample without field cooling from the cubic phase (light blue) and after field cooling under applied 400 V (dark blue). On the side, schematics of BTO unit cells for (001) and (010) are shown.

factor [Fig. 5(b)], defined as a mean square deviation of the cell parameters from their average. Notice that anisotropy vanishes at $a = 3.815$ and 3.78 Å for FM and A-AFM order, respectively, corresponding to the three-dimensional cubic structures, while a_0 corresponds to a large ($\approx 5\%$) anisotropy.

The results for orthorhombic LSMO (i.e., with rectangular substrate) are shown in Figs. 5(c) and 5(d). The general trend observed in the calculations is that for $b/a < 1$ the FM phase gains stability over the A-AFM one. The turnaround occurs at $b/a = 0.95$ for $a = 4$ Å, and the b/a value approaches 1 as a is decreased. For $b/a > 1$, on the other hand, the A-AFM phase is further strengthened with respect to the FM phase.

IV. DISCUSSION

There are four known mechanisms of magnetoelectric coupling: iron migration, charge accumulation/depletion, strain mediated, and exchange mediated. Since the BTO substrate is not magnetic, the last case can be excluded. The fact that XAS line shape does not change rules out ion migration as a possible cause: the chemical environment of Mn remains the same. Charge effects can also be excluded, since the detected XMCD signal is invariant for electric polarization reversal. Therefore, strain-mediated magnetoelectric coupling is the only possible explanation of the observed phenomena. In the following, the experimental results are interpreted according to this view, supported by the simulations described in the previous section.

LSMO in the 20–35% doping range is FM in the bulk whereas for epitaxially grown strained thin films the magnetic ordering may be different [39–42]. The magnetic ordering in LSMO is the result of the interplay between superexchange and double-exchange interactions. The first is mediated by t_{2g} orbitals and favors AFM ordering, while the latter is mediated by e_g orbitals (z^2 or $x^2 - y^2$) and favors FM ordering. In bulk, the dominant contribution of Mn e_g coupling [via double exchange with O(p) orbitals] in both planar and longitudinal directions favors spin pairing in the three directions and overall FM ordering. An applied strain along a given direction determines an anisotropic redistribution of the e_g levels. In-plane tensile strain would cause a depletion of z^2 orbitals and charge accumulation in $x^2 - y^2$ orbitals, with a consequent strengthening of FM ordering in plane, and AFM superexchange interactions prevailing across different planes, along the orthogonal direction [40,43]. The results of our simulations are consistent with this picture: the c/a ratio is the key parameter governing e_g charge anisotropy, and consequently the magnetic ordering. Higher values of a correspond to smaller c/a values and higher anisotropy of the unit cell, pushing the system towards A-AFM ordering. FM ordering counteracts the effect of this charge redistribution, resulting in equilibrium c/a values systematically larger than those for the A-AFM phase. The interpretation of the results for $b/a \neq 1$ are consistent with the results for c/a and anisotropy factor [see Fig. 5(d) for the specific case $a = 3.89$ Å]: the decrease of b/a below unity increases the equilibrium c/a value and, in turn, decreases the anisotropy; this mechanism stabilizes the FM phase against the A-AFM. In tetragonal LSMO the turnaround occurred for c/a greater than 0.95–0.96. This behavior is substantially maintained even for the orthorhombic structures. Our analysis is also consistent with the results of previous

$a^-b^-c^+$ octahedral tilting pattern [this symmetry also characterizes the antiferromagnetic (AFM) LaMnO_3 end-point structure]. In the simulations, the interface plane lattice parameters a and b (either square or rectangular) were fixed, while the system was fully relaxed along the interface-perpendicular direction (c axis). A tight convergence threshold of 0.1 mRy/bohr was imposed to the forces. As for magnetic ordering, we considered ferromagnetic (FM) ordering and three different AFM orderings, i.e., A type, C type, and G type; in this way the nearest-neighbor interactions along all three directions were taken into account. The Sr doping level is 25% in all the calculations presented hereafter.

Two sets of simulations were performed: in the first set a squared substrate, i.e., with $a = b$, was imposed; this mimics LSMO grown on BTO at room temperature when polarized out of plane. In the second set we allowed $a \neq b$ to explore a possible tetragonal-to-orthorhombic symmetry lowering for LSMO. This could mimic the distortion imposed by the BTO substrate in correspondence with the transition from the T to the O phase. However, structural disorder and/or configurational entropy effects are not included in the supercell approach.

In Fig. 5(a) total-energy results for tetragonal LSMO (i.e., with squared substrate) for the four magnetic orderings are reported, as a function of the planar lattice parameter. FM and A-type AFM orderings tightly compete within the examined structural range; the others are much higher in energy and can be discarded. The A-AFM ordering prevails in most of the examined a range, and is enhanced by increasing a , which corresponds to epitaxial tensile strain. On the other hand, FM ordering is strengthened by compressive strain, and sets in for $a < 3.87$ Å. In their respective equilibrium structures (corresponding both to $a_0 \approx 3.95$ and 3.96 Å), FM and A-AFM orders differ by an energy of 25 meV/f.u. The interpretation of the FM vs A-AFM competition is enlightened by the calculated c/a ratio [Fig. 5(b)] which decreases for increasing a . Importantly, for any given a value, c/a is always smaller (by a factor ≈ 0.01 on average) for the A-AFM phase than for the FM phase. The smaller c/a ratio reflects a higher anisotropy

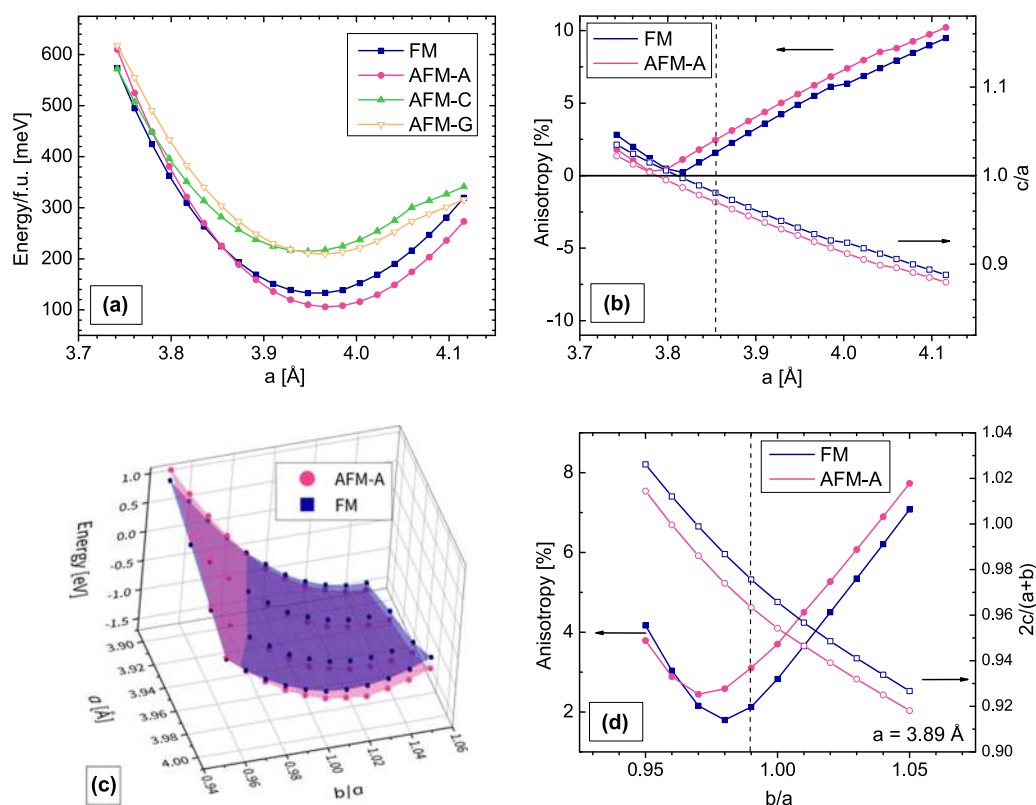


FIG. 5. Calculations of tetragonal LSMO film under planar strain: (a) energy per formula unit and (b) anisotropy factor (left axis) and c/a ratio (right axis). Calculations of orthorhombic $Pnma$ LSMO: (c) energy per cell as a function of both a and b/a and (d) example of anisotropy factor (left axis) and c/a ratio (right axis) for fixed $a = 3.89$ Å. In (b) and (d) the dashed lines correspond to the a and b/a values in which the FM and AFM phases have the same energy.

333 computational studies of phase transitions induced in LSMO
334 by compressive substrates [44].

335 The experimental results can now be interpreted: when BTO
336 is in the T phase and unbiased, the in-plane tensile strain
337 imposed on the LSMO film is large, favoring AFM order; in
338 this situation FM ordering is hindered also by the disorder
339 caused by the presence of multidomains (both in and out of
340 plane) in the BTO substrate. When BTO is polarized out of
341 plane, this disorder is reduced, and a cubic lattice is formed
342 at the interface; this is accompanied with a reduction of the
343 tensile strain imposed on the LSMO film, which favors the
344 appearance of FM ordering. Evidently, this effect dominates
345 over the loss of in-plane anisotropy, which acts contrariwise.
346 The XMCD signal observed in this case is, however, very small
347 (around 1%), indicating the competition between the effects
348 of these subtle distortions. It is also important to note that
349 the Curie temperature (T_C) of a tensile-strained LSMO film
350 is reduced with respect to the bulk value [26], and hence the
351 system could be close to the paramagnetic transition, with a
352 reduced magnetization.

353 When BTO is in the O phase, we could expect the polar-
354 ization vector to point 45° from the film plane, resulting in
355 the formation of a (pseudo-)rectangular lattice at the interface.
356 Even in this case there is a competition between the small
357 increase of the substrate lattice area and the uniaxial deforma-
358 tion in determining the anisotropy of the LSMO unit cell. Our
359 measurements indicate that the second effect is overcoming
360 the first one, resulting in an overall stronger FM order of the

361 LSMO film with respect to the T phase. This may be due even
362 to the lowering of the temperature. Indeed, the intensity of
363 the dichroic signal is reduced with the increase of temperature
364 already in the O phase, vanishing in the case of polarized BTO
365 at a temperature close to 320 ± 15 K [see Fig. 4(b)], which
366 can be assumed as the T_C of the polarized case, a value smaller
367 than that of bulk LSMO ($T_C = 369$ K) [25].

368 Finally, when BTO transforms from the O to the R phase, the
369 uniaxial deformation imposed on the LSMO film disappears,
370 but the average tensile strain is not relieved. This favors the
371 AFM ordering against FM ordering, and indeed no XMCD was
372 measured in this case. It results, therefore, that the structural
373 transition between R and O phases in BTO substrate leads to a
374 magnetic transition from AFM to FM ordering in LSMO thin
375 film the origin of which is strain driven.

376 It is interesting to notice that although the changes in the
377 BTO crystal parameters are lower than 1% the correspond-
378 ing magnetic effect on LSMO is sizeable. This once again
379 confirms the strong interplay between the orbital and spin
380 degrees of freedom in this transition-metal oxide, and how the
381 strain crucially affects the competition between FM and AFM
382 orderings. XMCD cannot provide the experimental evidence of
383 the existence of an AFM ordering; however, orbital anisotropy
384 was already demonstrated for LSMO epitaxial film grown on
385 substrates with a lower mismatch [39,45,46], so it is expected in
386 this case too, also taking into account the insulating behavior
387 observed from transport measurements in the R phase (see
388 Fig. 4).

Another aspect to be understood is the smallness of the XMCD signal observed compared to the value around 20% in the case of unstrained LSMO [36] (corresponding to a magnetization of $3.5 \mu_B/\text{Mn}$) [38]. As mentioned above, tensile stress in LSMO epitaxial films is known to decrease T_C , which implies that magnetization is severely reduced. Furthermore, our simulations show that AFM and FM orderings are in tight energetic competition for a wide range of lattice parameters. Several experimental and theoretical works (summarized in the review of Dagotto, Hotta, and Moreo [47]) have demonstrated the tendency of manganites to form an inhomogeneous state in which AFM and FM phases coexist, especially at the boundary of the phase diagram. Hence the changes of the Mn XMCD signal can be attributed to a variation of the FM fraction in the LSMO film, which is modulated by the substrate-induced strain. The smallness of this signal indicates that, in agreement with the simulations, the system would preferentially be AFM, but for some distortions of the substrate lattice it is pushed to the FM transition.

V. CONCLUSIONS

We employed XMCD to study the magnetic response of a 30-u.c. LSMO film deposited on BTO, and its dependence on the crystal structure of the substrate. The results show that the magnetic ordering of LSMO is extremely sensitive to the small distortions induced by the structural phase transitions of the substrate. In the case of pristine BTO substrate, with a large majority of in-plane BTO domains, magnetic dichroism is observed for the (intermediate) BTO O phase, whereas no magnetic dichroism is detected for the T (high temperature) and R (low temperature) phases. After setting by means of an external bias an out-of-plane polarization of the substrate, i.e., aligning the majority of BTO domains to the out-of-plane direction, magnetic dichroism is measured in the LSMO film at room temperature (BTO in the tetragonal phase).

These observations show that fine engineering of the interfacial strain is a suitable way towards electric control of the magnetic state in manganites. The subtle interplay between overall strain and uniaxial in-plane deformation governs the competition between FM and AFM orderings as reflected also by the *ab initio* calculations. The small changes in the LSMO epitaxial strain determined by changing the ratio between in-plane and out-of-plane domains in BTO substrate determine the transition between antiferromagnetism and ferromagnetism of the film.

VI. EXPERIMENTAL AND THEORETICAL METHODS

A thin film of 30 u.c. (≈ 12 nm) of $\text{La}_{0.65}\text{Sr}_{0.35}\text{MnO}_3$ has been deposited by molecular beam epitaxy on unpoled (100) BTO substrate from an ozone atmosphere with $p = 5 \times 10^{-7}$ mbar, with the substrate kept at 1000 K. RHEED assisted shuttered deposition developed by the Schlom group [48] allowed us to artificially repeat LSMO perovskite structure ($\text{AO} - \text{BO}_2$, A being $\text{La}_{0.65}\text{Sr}_{0.35}$ and B being Mn), with control of the stoichiometry of the film during deposition.

XAS and XMCD measurements at Mn $L_{2,3}$ edges were performed at APE-HE [29]. A total electron yield detection system was used, allowing a probing depth through the LSMO

layer of around 8 nm. Since the film is 12 nm thick, XMCD measurements probe a significant fraction of the volume of the film. A “magnetically dead layer” is known to form at the substrate/LSMO interface, especially in the presence of a high strain. This interfacial region is beyond the probing depth of the measurements here presented. Absorption measurements have been taken in circular polarization, with the sample at 45° with respect to the incident beam. To minimize possible artifacts, alternating magnetic field pulses of $+200$ and -200 Oe have been applied in the plane of the sample surface at each measured point of the absorption spectra; the difference between the two resulting curves gives the dichroic signal of the LSMO layer. The sample was cooled down to 100 K through a liquid nitrogen cooling system, and heated up to room temperature by a local heater. A thermocouple placed behind the sample holder allowed controlling the local temperature of the sample.

The sample was first characterized by XAS and XMCD with the BTO substrate in the pristine state. Then, the sample was capped with a thin (≈ 2 nm) gold layer, removed from the analysis chamber and mounted on a specific sample holder that allows us to set the out-of-plane polarization of the BTO substrate inside the analysis chamber [see Fig. 3(d)]. A MgO slab 0.5 mm thick was inserted under the sample to avoid electric contact between top and bottom of the sample. An electric bias up to 500 V could be applied with a Keithley 6485 picoammeter/voltage source, leading to a net polarization of the substrate in the out-of-plane direction, as confirmed by current vs voltage curves (I - V , see Supplemental Material [33]) and XRD characterizations. After setting the out-of-plane polarization, the sample was reintroduced in the analysis chamber and the XMCD characterization in temperature was repeated with the BTO polarized out of plane. For comparison between the “up” and “down” cases, the substrate was polarized *in situ* right before the XAS and XMCD measurements and the effect of the polarization switching was immediately checked with the acquisition of an I - V curve (see also the Supplemental Material [33]).

A second sample was grown in the exact same condition, but without any gold capping layer, and its structural and transport properties were studied. XRD measurements in Bragg-Brentano geometry were performed with PANALYTICAL'S EMPYREAN instrument [30] with Cu-K_α radiation at room temperature, i.e., with BTO in tetragonal phase. In the high-intensity mode the incident radiation is not monochromatic [Fig. 1(a)]. High-resolution XRD measurements were obtained in a double-axis configuration, using a 4-bounce Ge(220) monochromator to select only the $\text{Cu-K}_{\alpha 1}$ line (Fig. 4). The resistance of the LSMO film for different temperatures was measured in a four-probe van der Pauw configuration, with gold electrical contacts placed on the LSMO film surface.

First-principles calculations were performed using density-functional theory within generalized-gradient spin-density approximation, as implemented in the QUANTUM ESPRESSO code [49]. For our calculations we employed a basis set of plane waves and ultrasoft pseudopotentials with cutoff energies of 40 Ry, a $4 \times 4 \times 4$ k -point grid (corresponding to 32 *ab initio* k points in the irreducible Brillouin zone), and Gaussian smearing of 0.005 Ry. Fully relaxed 20-atom supercells were used for all the examined magnetic orderings; doping was treated by actual atomic substitutions.

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